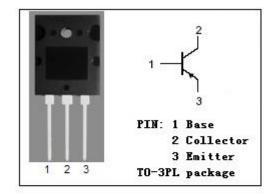


isc Silicon PNP Power Transistor

DESCRIPTION

- · High Current Capability
- · High Power Dissipation
- · Collector-Emitter Breakdown Voltage-
 - : V_{(BR)CEO}= -180V(Min)
- Complement to Type 2SD2155
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



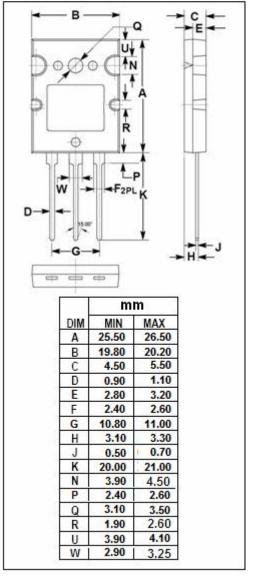
APPLICATIONS



- · Power amplifier applications
- Recommend for 100W high fidelity audio frequency amplifier output stage applications

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|---|-------|--------------|--|
| V _{СВО} | Collector-Base Voltage | -180 | V | |
| V _{CEO} | Collector-Emitter Voltage | -180 | ٧ | |
| V _{EBO} | Emitter-Base Voltage | -5 | V | |
| lc | Collector Current-Continuous | -15 | Α | |
| I _B | Base Current-Continuous | -1.5 | Α | |
| Pc | Collector Power Dissipation @ T _C =25℃ | 150 | W | |
| TJ | Junction Temperature 150 | | $^{\circ}$ C | |
| T _{stg} | Storage Temperature Range -55~150 | | | |





isc Silicon PNP Power Transistor

ELECTRICAL CHARACTERISTICS

T_{C} =25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---|------|------|------|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = -30mA ; I _B = 0 | -180 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = -8A; I _B = -0.8A | | | -3.0 | V |
| V _{BE(on)} | Base-Emitter On Voltage | I _C = -6A ; V _{CE} = -5V | | | -1.5 | V |
| I _{CBO} | Collector Cutoff Current | V _{CB} = -180V ; I _E = 0 | | | -5 | μА |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = -5V; I _C = 0 | | | -5 | μА |
| h _{FE-1} | DC Current Gain | I _C = -1A; V _{CE} = -5V | 55 | | 160 | |
| h _{FE-2} | DC Current Gain | Ic= -6A ; VcE= -5V | 30 | | | |
| Сов | Output Capacitance | I _E = 0; V _{CB} = -10V; ftest= 1.0MHz | | 340 | | pF |
| f⊤ | Current-Gain—Bandwidth Product | I _C = -1A ; V _{CE} = -5V | | 10 | | MHz |

♦ h_{FE-1} Classifications

| R | 0 | | | |
|--------|--------|--|--|--|
| 55-110 | 80-160 | | | |



isc Silicon PNP Power Transistor

2SB1429

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